	1	Type Hite		
<u></u>		1	7''''	DBs
_	BRS	(S 191069	nosfet or (metal adj oxide adj semiconducor adj (fet USPAT; US-PGPUB; EPO; or field)) or pmos or cmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT;
7	BRS	S 16687	sti or shallow adj trench	USPAT; US-PGPUB; EPO; JPO: DERWENT.
~	BDO	i		IBM_TDB
>	אַם אַם	90054	Ī	USPAT; US-PGPUB; EPO; JPO; DERWENT;
4	BRS	<u>හ</u>	indium near8 (corner or edge or next or adjacent\$4) USPAT; US-PGPUB; EPO; near4 (sti or shallow adj trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT;
5	IS&R	<u> </u>	(("6162679") or ("5960276") or ("6228726") or ("5296392") or ("6277697") or ("6245639") or	IBM_TDB
9	BRS	2	indium near8 (sti or shallow adj trench)	USPAT; US-PGPUB; EPO;
	BRS	3	next or adjacent\$4)	IBM_TDB USPAT; US-PGPUB: EPO:
			(indium pear8 /cti or chall	JPO; DERWENT;
8	BRS	4	(indium near8 (corner or edge or next or adjacent\$4) near4 (sti or shallow adjacent\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT;
о	BRS	16687	v adj trench	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT:
10	BRS	191069	mosfet or (metal adj oxide adj semiconducor adj (fet	3M_TDB SPAT; US-PGPUB; EPO;
			United by the second of the se	JPO, DEKWENT; IBM_TDB

	Type	Hits	Search Text	DBs
17	BRS 80	80	gate near2 (over or top or contact\$4) near2 (sti or shallow adj trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	78	(gate near2 (over or top or contact\$4) near2 (sti or shallow adj trench)) and (@ad < "20030714")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS 68	89	(gate near2 (amorphous or alpha or undop\$4 or intrinsic) near2 (polysilicon or polysi or poly adj (silicon or si)) and (sti or shallow adj trench)) and (@ad < "20030714")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS 2210	2210	(sti or shallow adj trench).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS 607	209	(sti or shallow adj trench).ti.	USPAT
16	IS&R 3083	3083	((257/506) or (257/510) or (257/519) or (257/E21.546) or (438/435)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB